

# NTTFS4932N

## MOSFET – Power, Single, N-Channel, $\mu$ 8FL 30 V, 79 A

### Features

- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### Applications

- Low-Side DC-DC Converters
- Power Load Switch
- Notebook Battery Management
- Motor Control

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Value	Unit	
Drain-to-Source Voltage	$V_{DSS}$	30	V	
Gate-to-Source Voltage	$V_{GS}$	$\pm 20$	V	
Continuous Drain Current $R_{\theta JA}$ (Note 1)	$I_D$	$T_A = 25^\circ\text{C}$	18	A
		$T_A = 85^\circ\text{C}$	13	
Power Dissipation $R_{\theta JA}$ (Note 1)	$P_D$	2.2	W	
Continuous Drain Current $R_{\theta JA} \leq 10$ s (Note 1)	$I_D$	$T_A = 25^\circ\text{C}$	25.5	A
		$T_A = 85^\circ\text{C}$	18.5	
Power Dissipation $R_{\theta JA} \leq 10$ s (Note 1)	$P_D$	4.5	W	
Continuous Drain Current $R_{\theta JA}$ (Note 2)	$I_D$	$T_A = 25^\circ\text{C}$	11	A
		$T_A = 85^\circ\text{C}$	8.0	
Power Dissipation $R_{\theta JA}$ (Note 2)	$P_D$	0.85	W	
Continuous Drain Current $R_{\theta JC}$ (Note 1)	$I_D$	$T_C = 25^\circ\text{C}$	79	A
		$T_C = 85^\circ\text{C}$	57	
Power Dissipation $R_{\theta JC}$ (Note 1)	$P_D$	43	W	
Pulsed Drain Current	$T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$	$I_{DM}$	235	A
Operating Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$	
Source Current (Body Diode)	$I_S$	39	A	
Drain to Source dV/dt	dV/dt	6.0	V/ns	
Single Pulse Drain-to-Source Avalanche Energy ( $T_J = 25^\circ\text{C}, V_{DD} = 50$ V, $V_{GS} = 10$ V, $I_L = 43$ A <sub>pk</sub> , $L = 0.1$ mH, $R_G = 25 \Omega$ )	$E_{AS}$	92.4	mJ	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	$T_L$	260	$^\circ\text{C}$	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

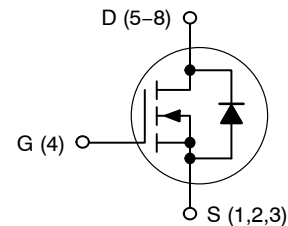


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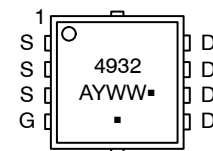
<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	$I_D$ MAX
30 V	4.0 m $\Omega$ @ 10 V	79 A
	5.5 m $\Omega$ @ 4.5 V	

### N-Channel MOSFET



### MARKING DIAGRAM



4932 = Specific Device Code  
 A = Assembly Location  
 Y = Year  
 WW = Work Week  
 ■ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping†
NTTFS4932NTAG	WDFN8 (Pb-Free)	1500/Tape & Reel
NTTFS4932NTWG	WDFN8 (Pb-Free)	5000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# NTTFS4932N

1. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.
2. Surface-mounted on FR4 board using the minimum recommended pad size.

## THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	2.9	°C/W
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	56.5	
Junction-to-Ambient – Steady State (Note 4)	$R_{\theta JA}$	147.6	
Junction-to-Ambient – ( $t \leq 10$ s) (Note 3)	$R_{\theta JA}$	27.5	

3. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.
4. Surface-mounted on FR4 board using the minimum recommended pad size (40 mm<sup>2</sup>, 1 oz. Cu).

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0$ V, $I_D = 250$ $\mu$ A	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			14		mV/°C
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0$ V, $V_{DS} = 24$ V	$T_J = 25^\circ\text{C}$		1.0	$\mu$ A
			$T_J = 125^\circ\text{C}$		10	
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{DS} = 0$ V, $V_{GS} = \pm 20$ V			$\pm 100$	nA

### ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$ , $I_D = 250$ $\mu$ A	1.2	1.6	2.2	V	
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			4.5		mV/°C	
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10$ V	$I_D = 20$ A		2.5	4.0	m $\Omega$
			$I_D = 10$ A		2.5		
		$V_{GS} = 4.5$ V	$I_D = 20$ A		3.6	5.5	
			$I_D = 10$ A		3.6		
Forward Transconductance	$g_{FS}$	$V_{DS} = 1.5$ V, $I_D = 15$ A		46		S	

### CHARGES AND CAPACITANCES

Input Capacitance	$C_{iss}$	$V_{GS} = 0$ V, $f = 1.0$ MHz, $V_{DS} = 15$ V		3111		pF
Output Capacitance	$C_{oss}$			1064		
Reverse Transfer Capacitance	$C_{rss}$			42		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5$ V, $V_{DS} = 15$ V, $I_D = 20$ A		20		nC
Threshold Gate Charge	$Q_{G(TH)}$			4.9		
Gate-to-Source Charge	$Q_{GS}$			8.9		
Gate-to-Drain Charge	$Q_{GD}$			3.3		
Total Gate Charge	$Q_{G(TOT)}$		$V_{GS} = 10$ V, $V_{DS} = 15$ V, $I_D = 20$ A		46.5	

### SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 4.5$ V, $V_{DS} = 15$ V, $I_D = 15$ A, $R_G = 3.0$ $\Omega$		15.5		ns
Rise Time	$t_r$			22.6		
Turn-Off Delay Time	$t_{d(off)}$			29		
Fall Time	$t_f$			4.8		

5. Pulse Test: pulse width = 300  $\mu$ s, duty cycle  $\leq 2\%$ .
6. Switching characteristics are independent of operating junction temperatures.

# NTTFS4932N

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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### SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 15 V, I <sub>D</sub> = 15 A, R <sub>G</sub> = 3.0 Ω		11		ns
Rise Time	t <sub>r</sub>			21.5		
Turn-Off Delay Time	t <sub>d(off)</sub>			35.6		
Fall Time	t <sub>f</sub>			3.5		

### DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 20 A	T <sub>J</sub> = 25°C		0.8	1.1	V
			T <sub>J</sub> = 125°C		0.7		
Reverse Recovery Time	t <sub>RR</sub>	V <sub>GS</sub> = 0 V, dI <sub>S</sub> /dt = 100 A/μs, I <sub>S</sub> = 20 A			40		ns
Charge Time	t <sub>a</sub>				21		
Discharge Time	t <sub>b</sub>				19		
Reverse Recovery Charge	Q <sub>RR</sub>				37.5		nC

### PACKAGE PARASITIC VALUES

Source Inductance	L <sub>S</sub>	T <sub>A</sub> = 25°C		0.38		nH
Drain Inductance	L <sub>D</sub>			0.054		
Gate Inductance	L <sub>G</sub>			1.3		
Gate Resistance	R <sub>G</sub>			1.1	2.0	

5. Pulse Test: pulse width = 300 μs, duty cycle ≤ 2%.  
 6. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

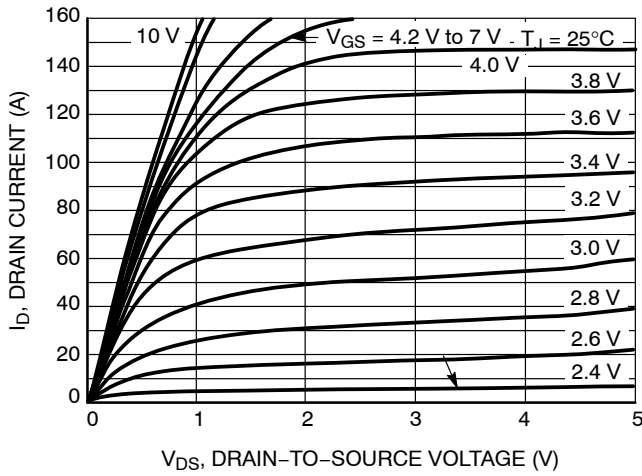


Figure 1. On-Region Characteristics

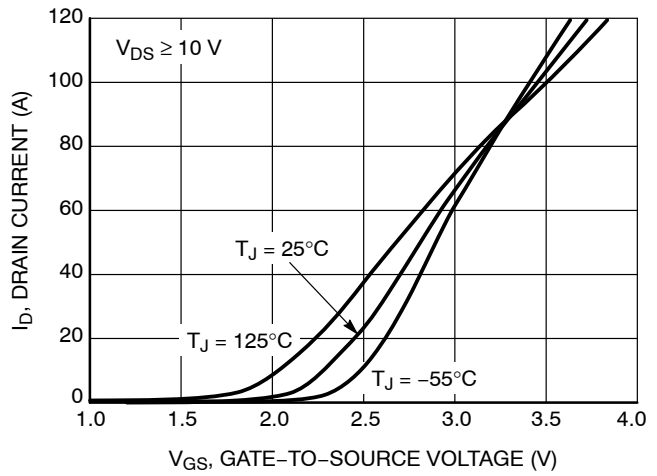


Figure 2. Transfer Characteristics

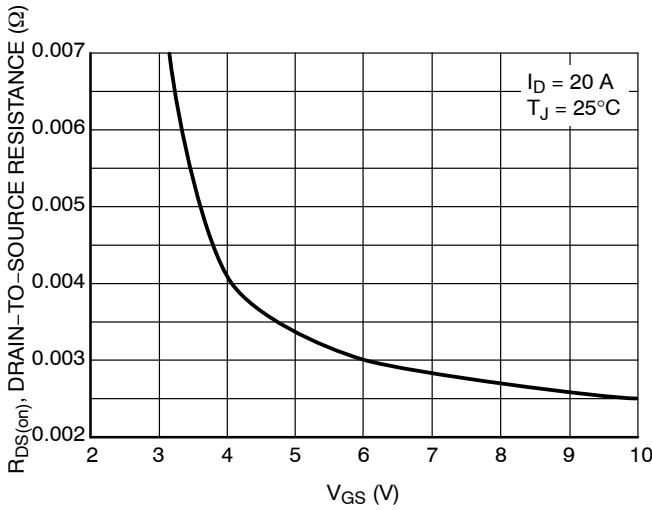


Figure 3. On-Resistance vs.  $V_{GS}$

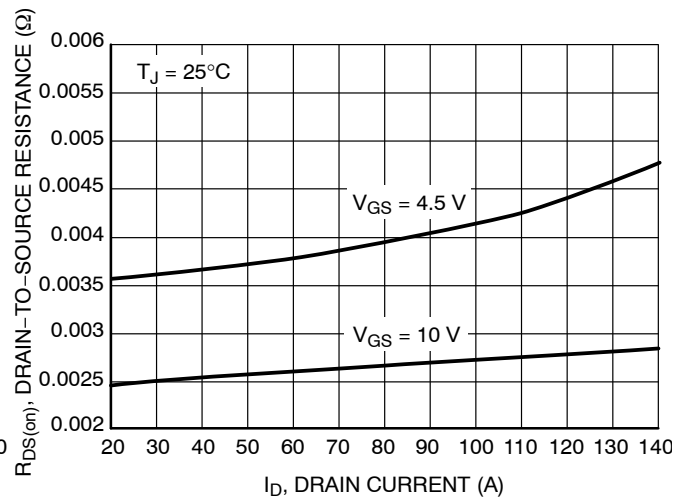


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

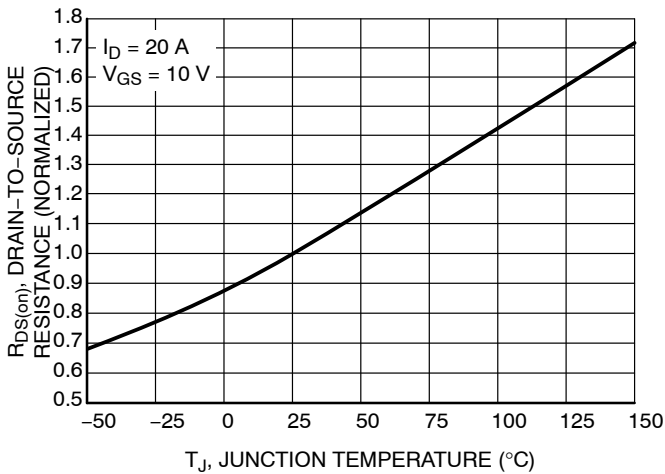


Figure 5. On-Resistance Variation with Temperature

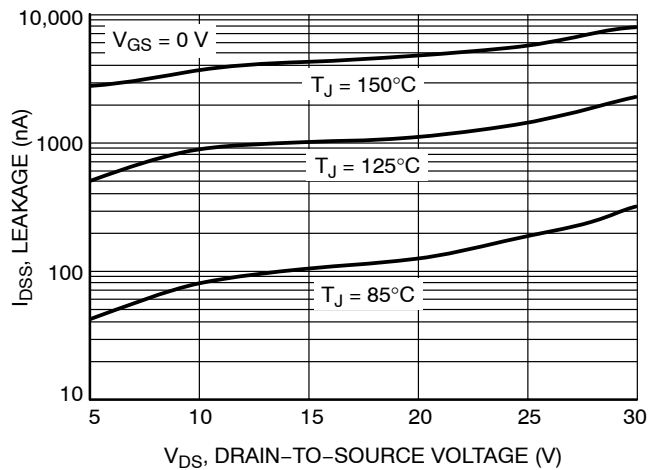


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

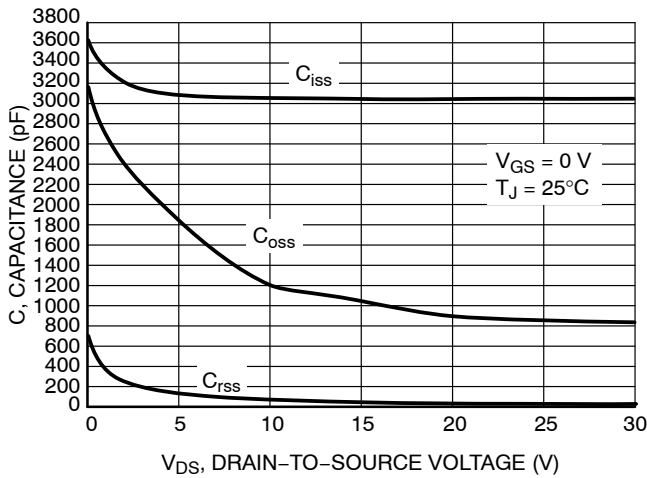


Figure 7. Capacitance Variation

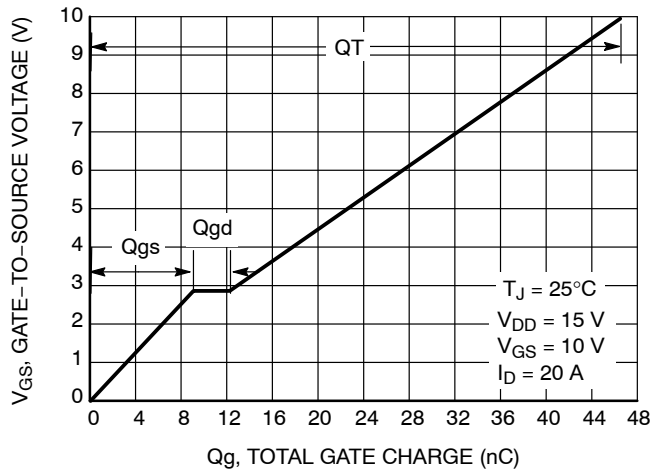


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

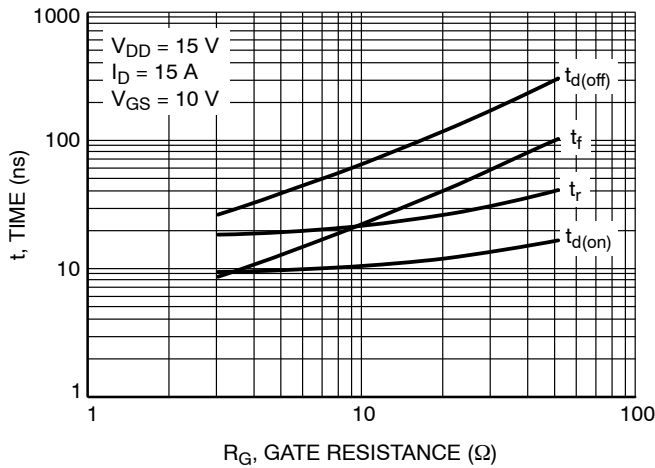


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

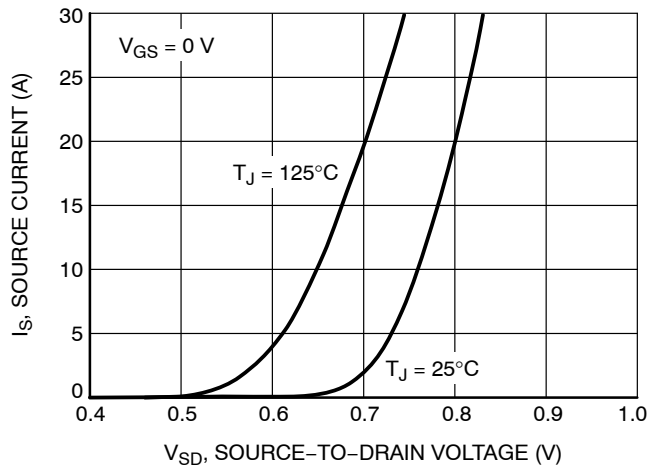


Figure 10. Diode Forward Voltage vs. Current

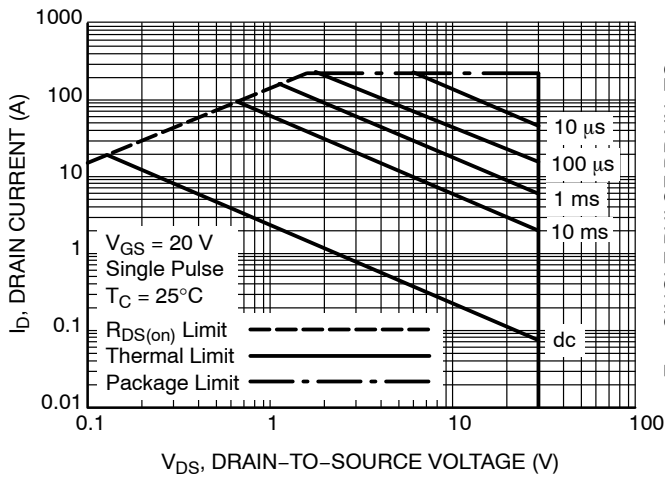


Figure 11. Maximum Rated Forward Biased Safe Operating Area

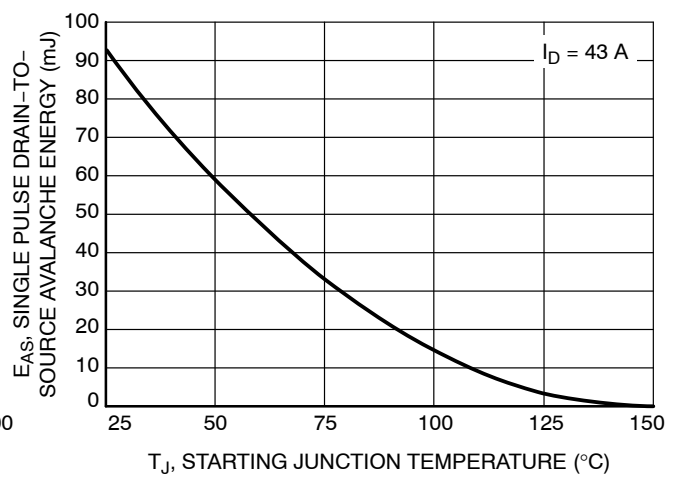


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

# NTTFS4932N

## TYPICAL CHARACTERISTICS

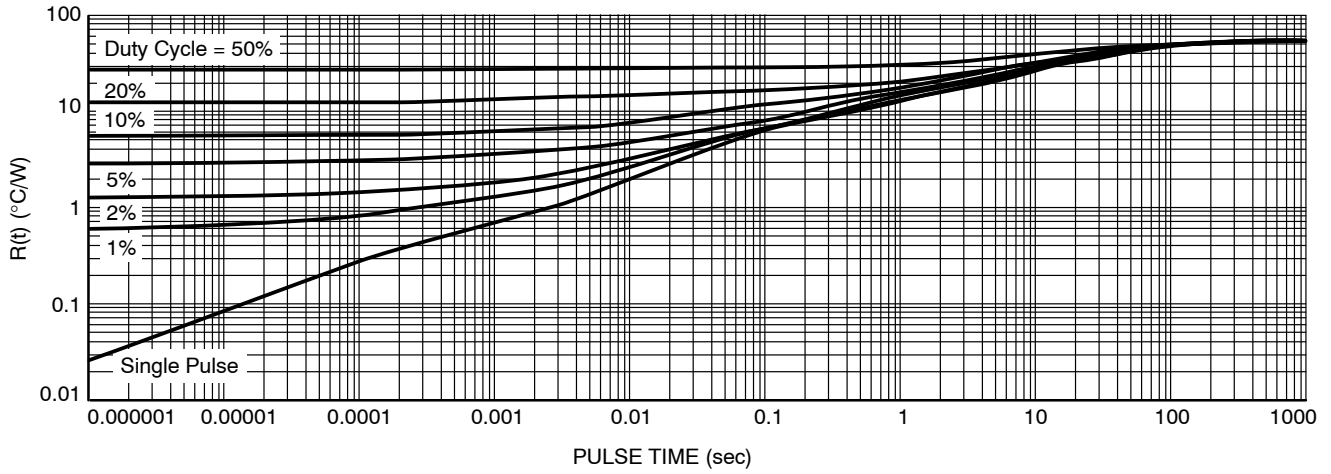


Figure 13. Thermal Response

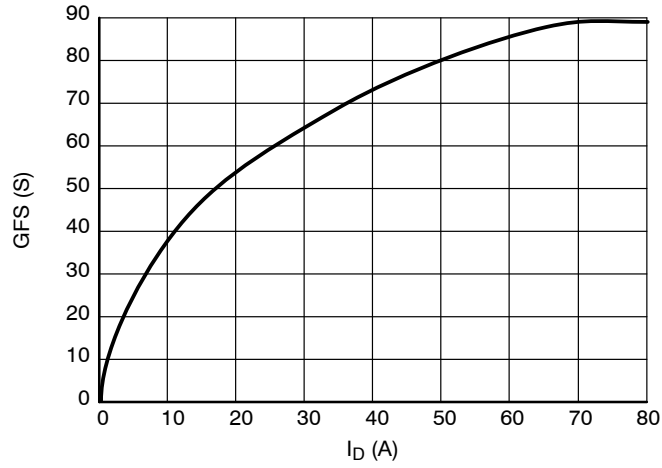


Figure 14. GFS vs.  $I_D$

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

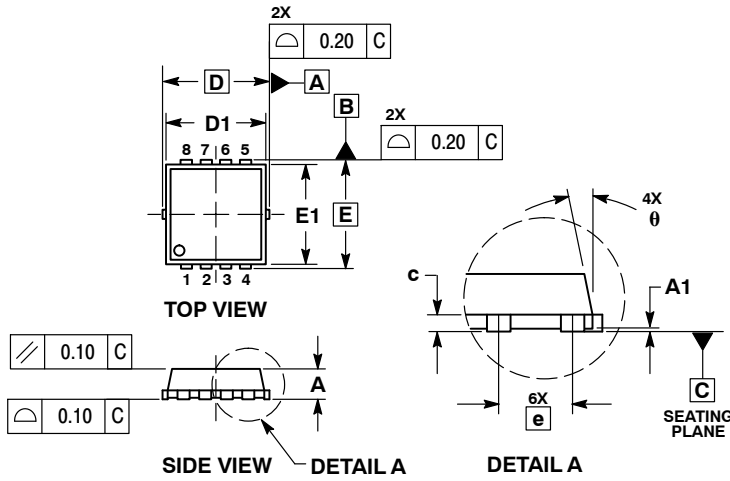
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SCALE 2:1

## WDFN8 3.3x3.3, 0.65P CASE 511AB ISSUE D

DATE 23 APR 2012



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.75	0.80	0.028	0.030	0.031
A1	0.00	---	0.05	0.000	---	0.002
b	0.23	0.30	0.40	0.009	0.012	0.016
c	0.15	0.20	0.25	0.006	0.008	0.010
D	3.30 BSC			0.130 BSC		
D1	2.95	3.05	3.15	0.116	0.120	0.124
D2	1.98	2.11	2.24	0.078	0.083	0.088
E	3.30 BSC			0.130 BSC		
E1	2.95	3.05	3.15	0.116	0.120	0.124
E2	1.47	1.60	1.73	0.058	0.063	0.068
E3	0.23	0.30	0.40	0.009	0.012	0.016
e	0.65 BSC			0.026 BSC		
G	0.30	0.41	0.51	0.012	0.016	0.020
K	0.65	0.80	0.95	0.026	0.032	0.037
L	0.30	0.43	0.56	0.012	0.017	0.022
L1	0.06	0.13	0.20	0.002	0.005	0.008
M	1.40	1.50	1.60	0.055	0.059	0.063
θ	0°	---	12°	0°	---	12°

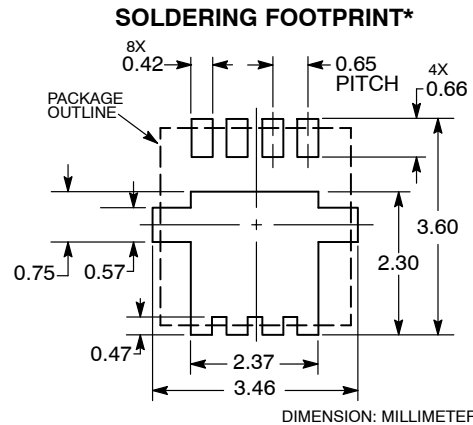


### GENERIC MARKING DIAGRAM\*



- XXXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- WW = Work Week
- = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking.  
Pb-Free indicator, "G" or microdot "▪", may or may not be present.



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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